



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	RDS(ON) max	Ι _D Τ _A = +25°C
	77mΩ@ V _{GS} = -10V	-3.5A
-30V	95mΩ@ V _{GS} = -4.5V	-3.0A
	150mΩ@ V _{GS} = -2.5V	-2.4A

Description and Applications

This MOSFET has been designed to meet the stringent requirements of Automotive applications. It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

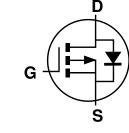
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (@3)
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)

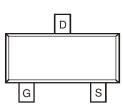


SOT23

Top View







Top View

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3130LQ-7	SOT23	3000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



 $\begin{array}{l} P5S = Product Type Marking Code \\ YM or \overline{Y}M = Date Code Marking \\ Y or \overline{Y} = Year (ex: D = 2016) \\ M = Month (ex: 9 = September) \end{array}$

Date Code Key

Notes:

Buie boue rie	-	1								1		
Year	2016		2017	2018	2018 2019		2019 2020		2021	2022		2023
Code	D		E	F	G		G H		I	J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	-30	V	
Gate-Source Voltage		V _{GSS}	±12	V	
	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-3.5 -2.6	А
Continuous Drain Current (Note 6) $V_{GS} = -4.5V$	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-4.1 -3.2	А
Maximum Continuous Body Diode Forward Curren	t (Note 6)	Is	-1.6	А	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-20	А	

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissinction (Note 6)	$T_A = +25^{\circ}C$	Р	0.7	W
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	0.4	vv
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	P	184	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ extsf{ heta}JA}$	115	C/W
Tetal Dower Dissinction (Note 7)	$T_A = +25^{\circ}C$	D	1.3	W
Total Power Dissipation (Note 7)	T _A = +70°C	PD	0.8	vv
Thermal Desistance, Junction to Ambient (Note 7)	Steady State	P	94	
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{ heta JA}$	61	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	25		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

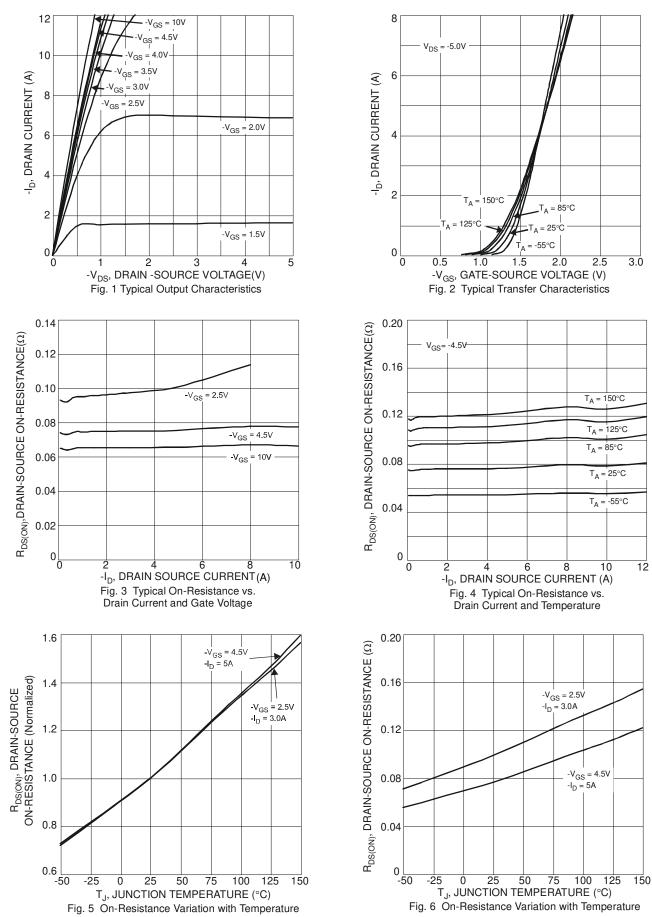
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}		—	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Body Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)	•					*
Gate Threshold Voltage	V _{GS(TH)}	-0.6	—	-1.3	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
		_	59	77		V _{GS} = -10V, I _D = -4.2A
Static Drain-Source On-Resistance	R _{DS(ON)}	_	73	95	mΩ	$V_{GS} = -4.5V, I_D = -4A$
		_	115	150		$V_{GS} = -2.5V, I_D = -3A$
Forward Transconductance	g fs	_	8	_	S	$V_{DS} = -5V, I_D = -4A$
Source-Drain Diode Forward Voltage	V _{SD}	_	-0.8	-1.25	V	$V_{GS} = 0V, I_{S} = -3.0A$
DYNAMIC CHARACTERISTICS (Note 9)						÷
Input Capacitance	Ciss		432	864	pF pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	Coss		87	174		
Reverse Transfer Capacitance	Crss		62	124	pF	
Gate Resistance	RG	_	4.04	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS (Note 9)	•					÷
Total Gate Charge	QG		5.9	11.8		$V_{DS} = -15V, V_{GS} = -4.5V, I_D = -4.0A$
Total Gate Gharge	QG		12	24	nC	$V_{DS} = -15V, V_{GS} = -10V, I_D = -4.0A$
Gate-Source Charge	Q _{GS}		1.0	2.0	no	
Gate-Drain Charge	Q _{GD}	_	3.1	6.2		$V_{DS} = -15V, V_{GS} = -4.5V, I_D = -4.0A$
Turn-On Delay Time	t _{D(ON)}		4.6	9.2		
Rise Time	t _R		6.5	13.0		$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t _{D(OFF)}		27.8	55.6	ns	$I_D = -1A, R_G = 6.0\Omega$
Fall Time	t _F	_	15.0	30.0		

6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing

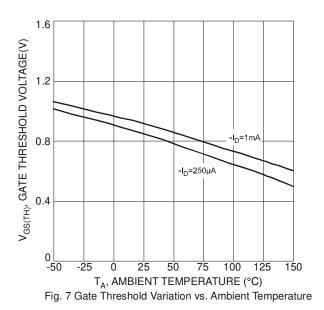
Notes:

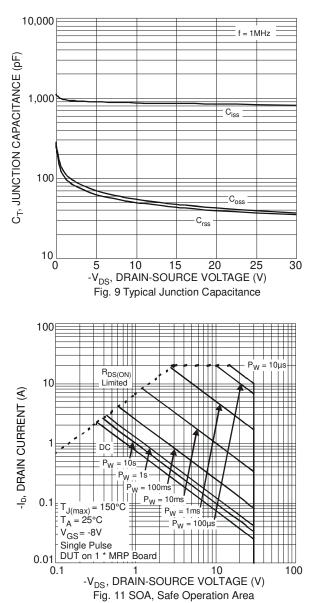


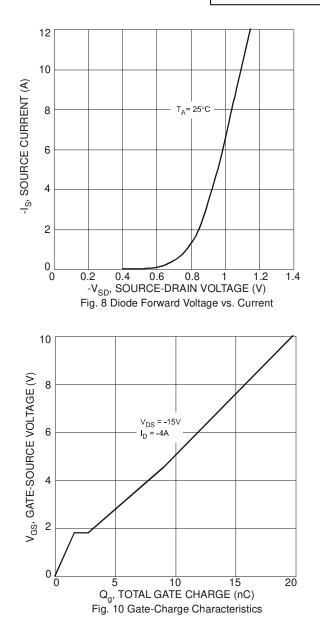


DMP3130LQ Document number: DS38728 Rev. 1 - 2 3 of 6 www.diodes.com

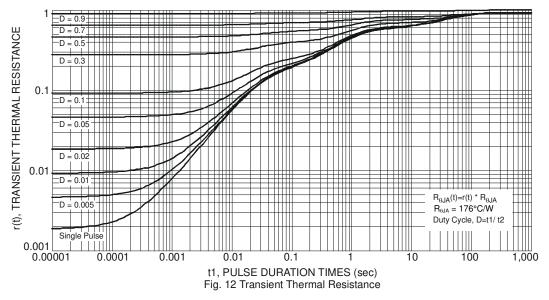






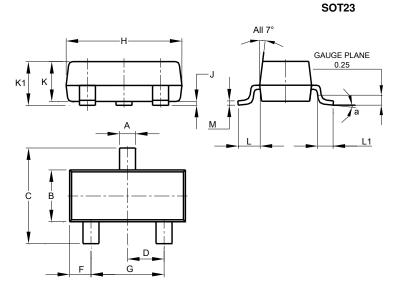






Package Outline Dimensions

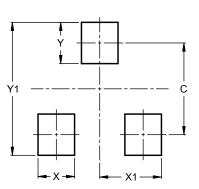
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Y	0.9			
Y1	2.9			

DMP3130LQ Document number: DS38728 Rev. 1 - 2



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2016, Diodes Incorporated

www.diodes.com